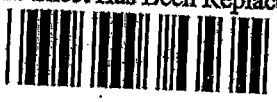
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ABSTRACT

A process for producing a semiconductor device, comprising the steps of providing a wafer of given thickness having a surface furnished with semiconductor circuits and a back; forming grooves of a cut depth smaller than the thickness of the wafer, said grooves extending from the wafer circuit surface; sticking a surface protective sheet onto the wafer circuit surface; grinding the back of the wafer so that the thickness of the wafer is reduced to thereby finally result in division of the wafer into individual chips with spaces therebetween; sticking a dicing/die bond sheet onto the ground back of the wafer, said dicing/die bond sheet comprising a base and, superimposed thereon, an adhesive layer, said adhering performed so that the adhesive layer is brought into contact with the ground back of the wafer; peeling the surface protective sheet from the wafer circuit surface to thereby cause the adhesive layer of the dicing/die bond sheet to be exposed through each space between neighboring individual chips; cutting the exposed adhesive layer of the dicing/die bond sheet; detaching the individual chips having the cut adhesive layer adhering thereto from the base of the dicing/die bond sheet; and bonding the individual chips through the

adhesive layer to a given substrate. This process is advantageous in that an appropriate amount of adhesive layer can easily be formed on the back of extremely thin chips to thereby enable avoiding chip breakage, chip cracking or package cracking, so that a productivity enhancement can be realized.

Figure 5

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